

## Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

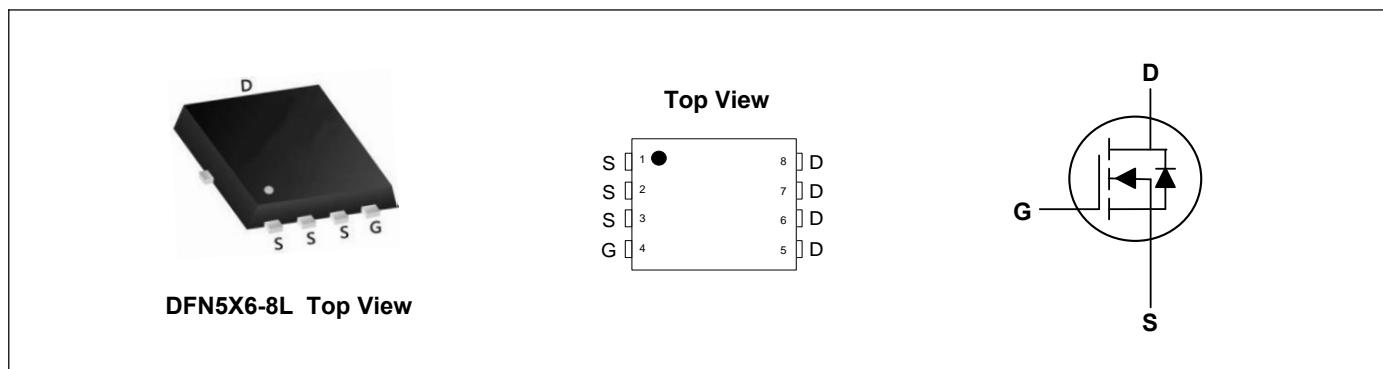
## Product Summary



$V_{DS}$	200	V
$I_D$	9	A
$R_{DS(ON)}$ (at $V_{GS}=10V$ )	210	mΩ

## Applications

- High Frequency Point-of-Load Synchronous Buck Converter
- Networking DC-DC Power System
- LCD/LED Back Light



## Absolute Maximum Ratings( $T_A=25^\circ C$ , unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	$V_{DS}$	200	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D @ T_c = 25^\circ C$	9	A
Continuous Drain Current	$I_D @ T_c = 100^\circ C$	6.3	A
Pulsed Drain Current <sup>1</sup>	$I_{DM}$	36	A
Single Pulse Avalanche Energy <sup>3</sup>	EAS	90	mJ
Total Power Dissipation	$P_D$	55	W
Derating factor		0.42	W/ $^\circ C$
Storage Temperature Range	$T_{STG}$	-55 to 150	$^\circ C$
Operating Junction Temperature Range	$T_J$	-55 to 150	$^\circ C$

## Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance Junction-Case <sup>1</sup>	$R_{\theta JC}$	---	1.6	$^\circ C/W$

**Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)**

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}$ , $I_{\text{D}}=250\mu\text{A}$	200	---	---	V
Static Drain-Source On-Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}$ , $I_{\text{D}}=4.5\text{A}$	---	180	210	$\text{m}\Omega$
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{GS}}=V_{\text{DS}}$ , $I_{\text{D}}=250\mu\text{A}$	2.5	3.5	4.5	V
Drain-Source Leakage Current	$I_{\text{DSS}}$	$V_{\text{DS}}=200\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $T_J=25^\circ\text{C}$	---	---	1	$\mu\text{A}$
Gate-Source Leakage Current	$I_{\text{GSS}}$	$V_{\text{GS}}=\pm 20\text{V}$ , $V_{\text{DS}}=0\text{V}$	---	---	$\pm 100$	nA
Forward Transconductance	$g_{\text{fs}}$	$V_{\text{DS}}=10\text{V}$ , $I_{\text{D}}=9\text{A}$	---	5	---	S
Total Gate Charge	$Q_g$	$V_{\text{DS}}=160\text{V}$ , $V_{\text{GS}}=10\text{V}$ , $I_{\text{D}}=4.5\text{A}$	---	18	---	nC
Gate-Source Charge	$Q_{\text{gs}}$		---	4.5	---	
Gate-Drain Charge	$Q_{\text{gd}}$		---	5.6	---	
Turn-On Delay Time	$T_{\text{d}(\text{on})}$	$V_{\text{DD}}=100\text{V}$ , $V_{\text{GS}}=10\text{V}$ , $R_{\text{G}}=5\Omega$	---	6.8	---	ns
Rise Time	$T_r$		---	10	---	
Turn-Off Delay Time	$T_{\text{d}(\text{off})}$		---	19	---	
Fall Time	$T_f$		---	9	---	
Input Capacitance	$C_{\text{iss}}$	$V_{\text{DS}}=25\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $f=1\text{MHz}$	---	540	---	pF
Output Capacitance	$C_{\text{oss}}$		---	80	---	
Reverse Transfer Capacitance	$C_{\text{rss}}$		---	22	---	

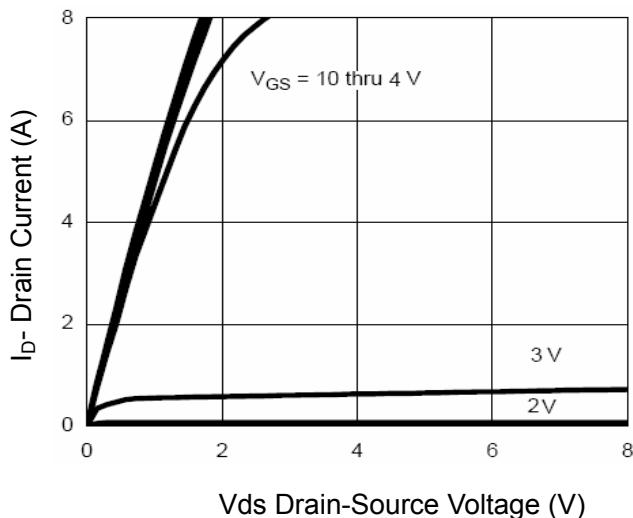
**Drain-Source Diode Characteristics**

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Continuous Source Current <sup>1</sup>	$I_s$		---	---	9	A
Diode Forward Voltage <sup>2</sup>	$V_{\text{SD}}$	$V_{\text{GS}}=0\text{V}$ , $I_s=9\text{A}$ , $T_J=25^\circ\text{C}$	---	---	1.0	V

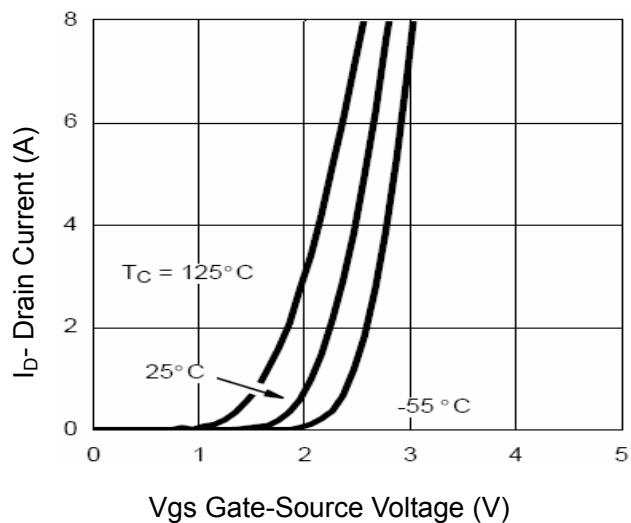
**Note:**

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu\text{s}$  , duty cycle  $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is  $V_{\text{DD}}=50\text{V}$ , $V_{\text{GS}}=10\text{V}$ , $L=0.5\text{mH}$ , $R_{\text{G}}=25\Omega$
- 4.The power dissipation is limited by  $150^\circ\text{C}$  junction temperature

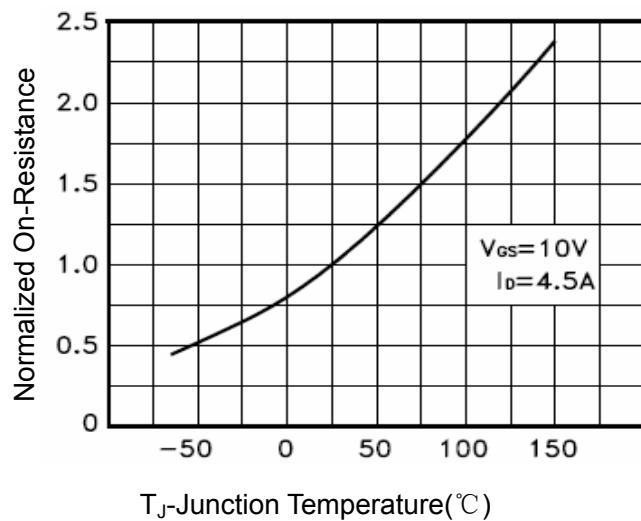
## Typical Characteristics



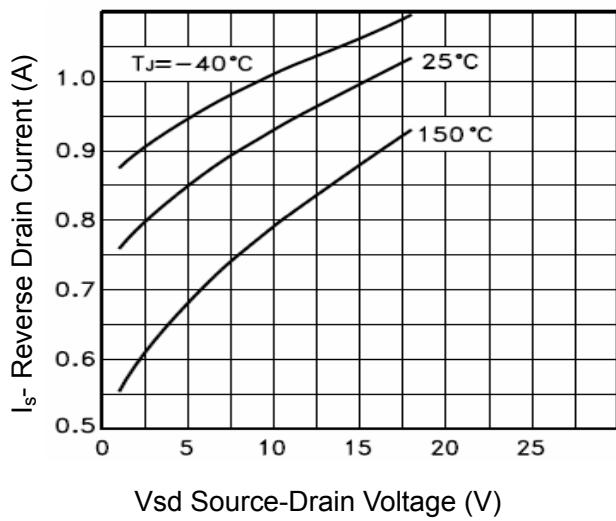
**Figure 1 Output Characteristics**



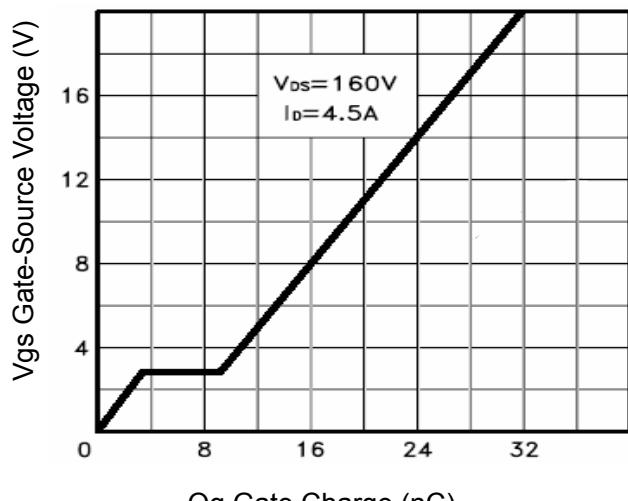
**Figure 2 Transfer Characteristics**



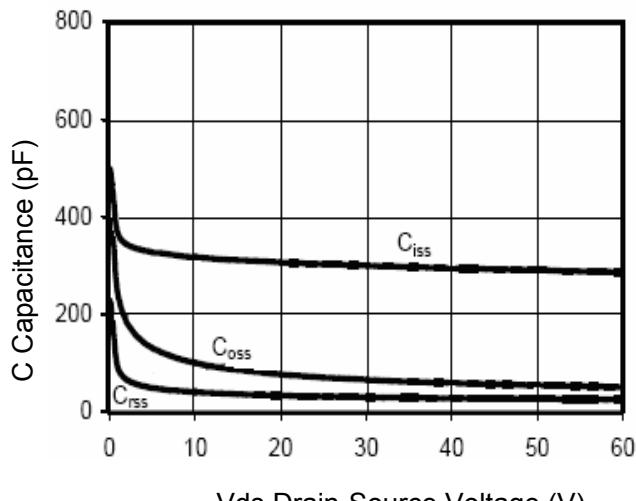
**Figure 3 Rdson-JunctionTemperature**



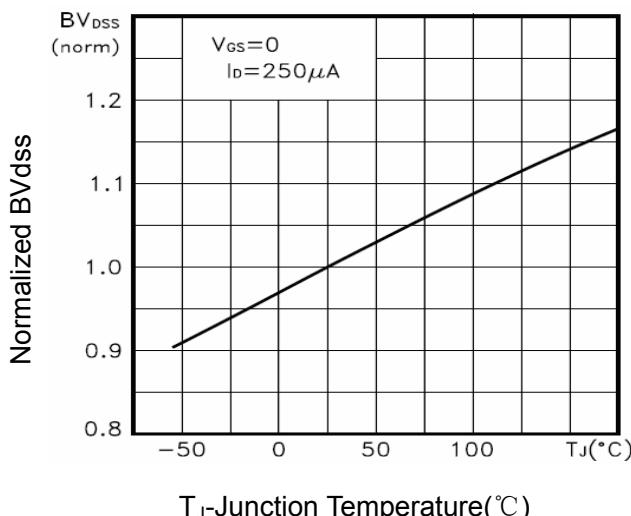
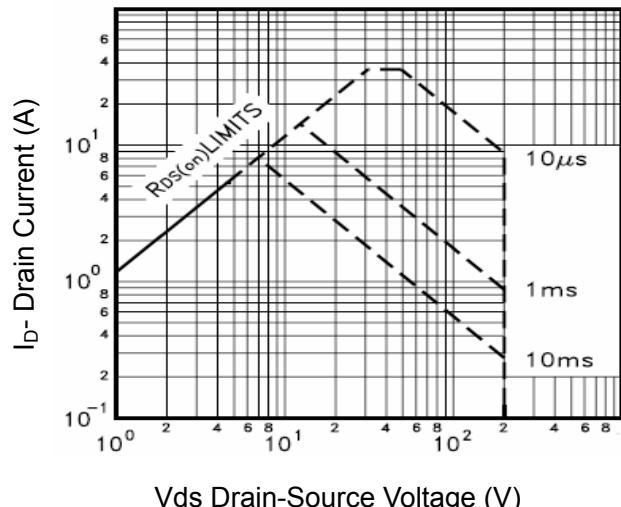
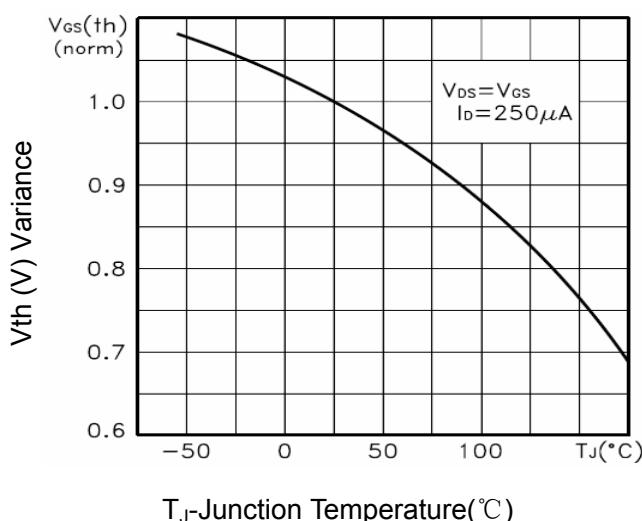
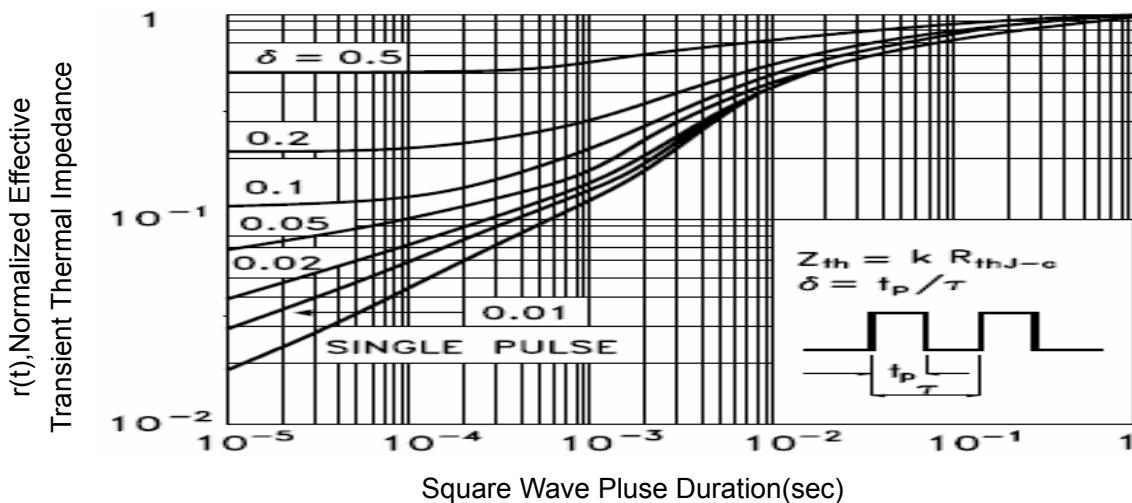
**Figure 4 Source- Drain Diode Forward**



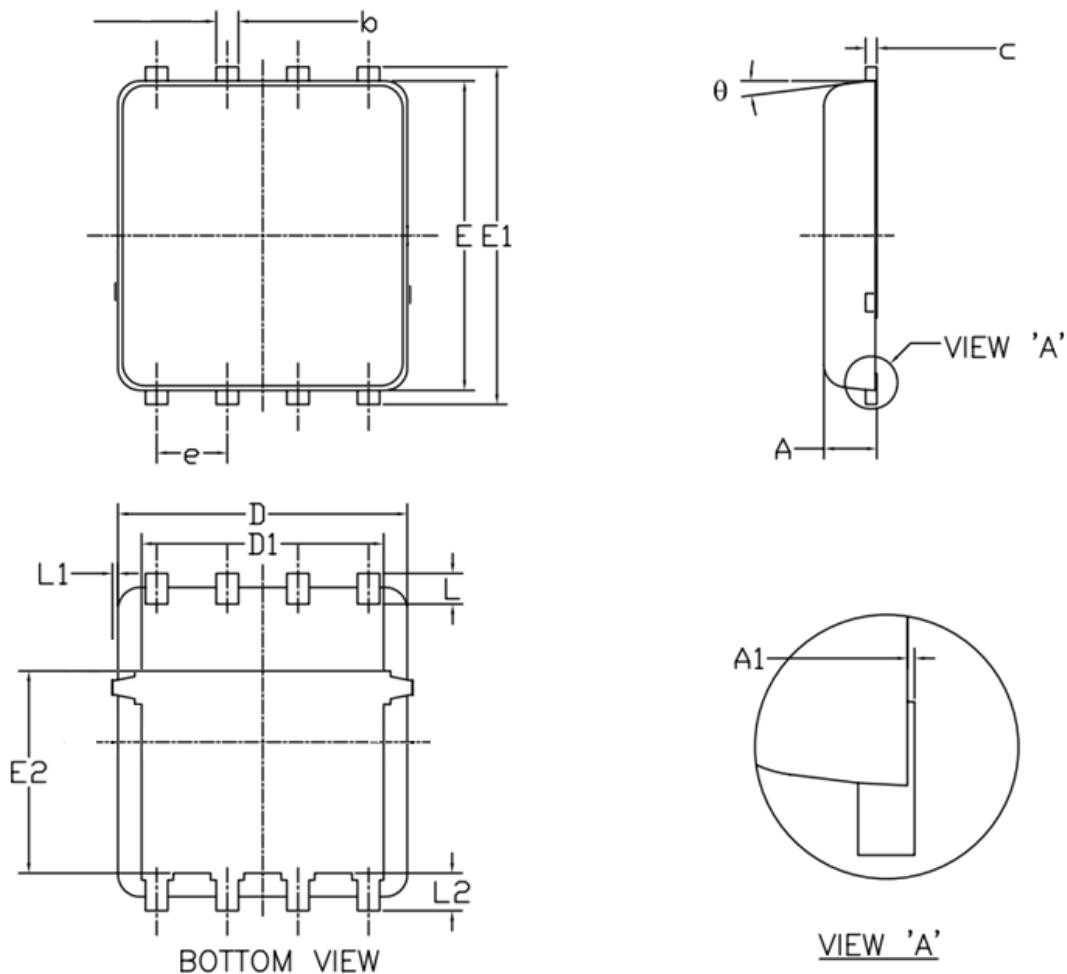
**Figure 5 Gate Charge**



**Figure 6 Capacitance vs Vds**


**Figure 7**  $BV_{DSS}$  vs Junction Temperature

**Figure 8** Safe Operation Area

**Figure 9**  $V_{GS(th)}$  vs Junction Temperature

**Figure 10** Normalized Maximum Transient Thermal Impedance

### DFN5X6-8L Package Outline Dimensions



<b>Symbol</b>	<b>Dimensions (unit:mm)</b>			<b>Symbol</b>	<b>Dimensions (unit:mm)</b>		
	<b>Min</b>	<b>Typ</b>	<b>Max</b>		<b>Min</b>	<b>Typ</b>	<b>Max</b>
<b>A</b>	0.90	1.00	1.20	<b>E1</b>	5.90	6.10	6.35
<b>A1</b>	0.00	--	0.05	<b>E2</b>	3.38	3.58	3.92
<b>b</b>	0.30	0.40	0.51	<b>e</b>	1.27 BSC		
<b>c</b>	0.20	0.25	0.33	<b>L</b>	0.51	0.61	0.71
<b>D</b>	4.80	4.90	5.40	<b>L1</b>	--	--	0.15
<b>D1</b>	3.61	4.00	4.25	<b>L2</b>	0.41	0.51	0.61
<b>E</b>	5.65	5.80	6.06	<b><math>\theta</math></b>	0°	--	12°